

**IN THE CLAIMS:**

Please amend the claims as follows:

1. (Currently amended) A chemical mechanical polishing method using a chemical o  
mechanical polishing apparatus comprising:

a polishing table including a rotation mechanism; [[,]]

a polishing pad attached on the polishing table; [[,]]

a substrate carrier for holding a member to be polished, said substrate carrier including a  
rotation mechanism and a pressurization mechanism; [[, and]]

a dresser including a rotation mechanism and a pressurization mechanism; [[,]]

a detector for detecting a state of a surface of the polishing pad; and

a controller for controlling a pressure to be applied by the dresser based on a signal from  
the detector, said method comprising the steps of:

(a) detecting the state of the surface of the polishing pad using the detector;

(b) controlling the pressure to be applied by the dresser using the controller;

(c) [[(a)]] dressing the polishing pad with the dresser coming in contact with the polishing  
pad; and

(d) [[(b)]] polishing the member to be polished a film using the polishing pad having a  
surface roughness of 6 $\mu$ m to 8 $\mu$ m inclusive in a pattern formation substrate including a substrate  
region in the top of which a trench is formed and the film with which the trench is filled in.

2. (Currently amended) The chemical mechanical polishing method of Claim 1, wherein  
in the step (b) [[(a)]], ~~a dressing pressure of~~ the pressure to be applied by the dresser is 18g/cm<sup>2</sup>  
to 40g/cm<sup>2</sup> inclusive is applied to the dresser.

3-4. (Canceled)

5. (Currently amended) The chemical mechanical polishing method of Claim 1, wherein the step (c) [(a)] and the step (d) [(b)] are carried out simultaneously.

6-10. (Canceled)

11. (New) The chemical mechanical polishing method of Claim 1, wherein a surface roughness of the polishing pad is  $6\mu\text{m}$  to  $8\mu\text{m}$ .

12. (New) The chemical mechanical polishing method of Claim 1, wherein the step (a), the step (b) and the step (c) are carried out simultaneously.

13. (New) The chemical mechanical polishing method of Claim 1, wherein in the step (a), the detector measures a rotational torque of the dresser.

14. (New) The chemical mechanical polishing method of Claim 1, wherein in the step (a), the detector irradiates the surface of the polishing pad with a laser beam and receives the laser beam reflected by the surface of the polishing pad to detect intensity of the laser beam reflected.

15. (New) The chemical mechanical polishing method of Claim 1, wherein in the step (a), the detector irradiates the surface of the polishing pad with an electromagnetic wave and receives the electromagnetic wave reflected by the surface of the polishing pad to detect intensity of the electromagnetic wave reflected.

16. (New) The chemical mechanical polishing method of Claim 1, wherein in the step (a), the detector transmits an electromagnetic wave to the surface of the polishing pad and receives the electromagnetic wave reflected by the surface of the polishing pad to measure a time required from when the electromagnetic wave is transmitted to when the electromagnetic wave reflected is received.